



# 200G per Lane for beyond 400GbE

- an update from the [7/27/2020 NEA presentation](#)

Cedric Lam, Xiang Zhou, and Hong Liu

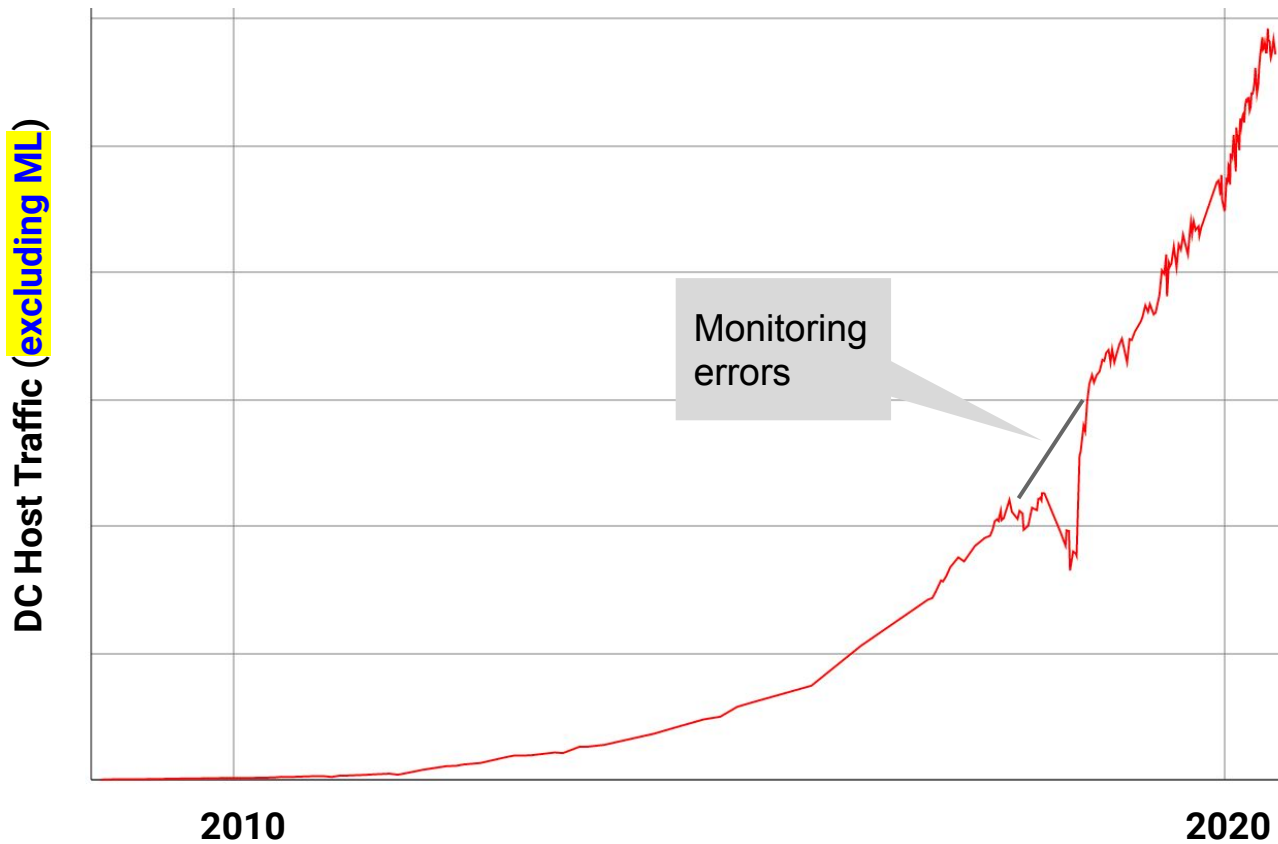
03/29/2021

IEEE 802.3 B400G SG Meeting

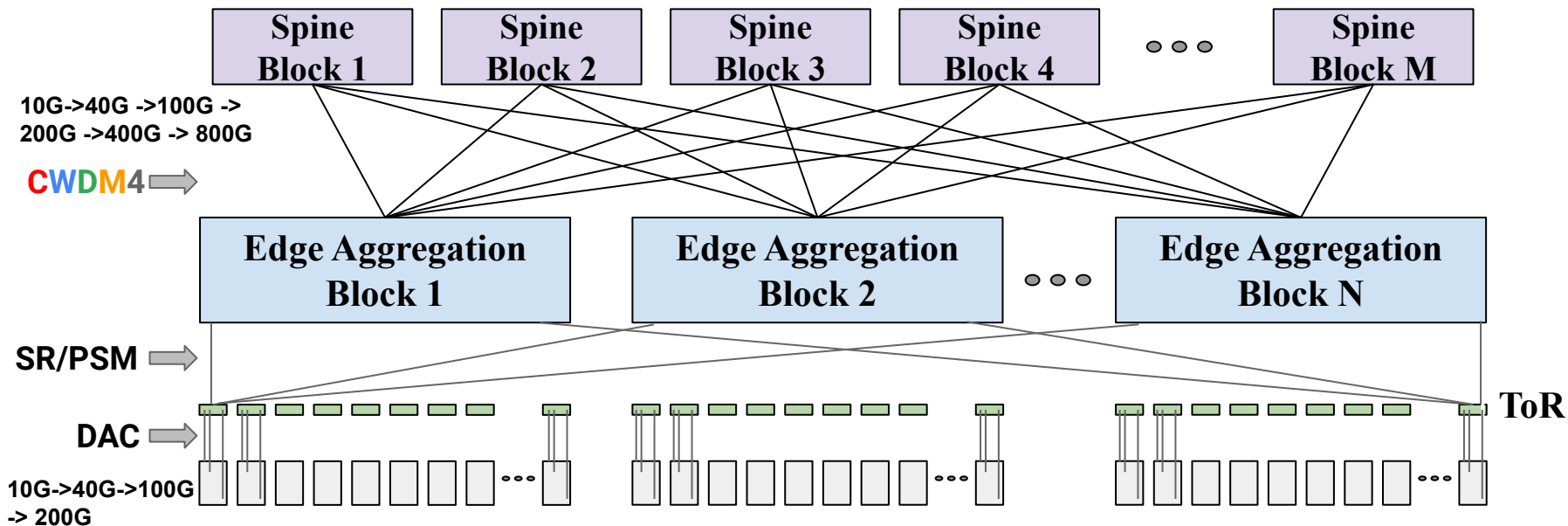
# Outline

- Driver and use cases for beyond 400G
- Justification for 200G per lane
  - Lower TCO
  - Scalability to 1.6T Ethernet
- 200G optical lane technical feasibilities
  - Baseline performance for different modulation format choices
  - Key component requirements
  - 200G per lane (optical) components readiness survey

# DC Traffic Continues to Grow Rapidly (Regular Servers)



# > 400GbE will be needed in DCN Fabrics

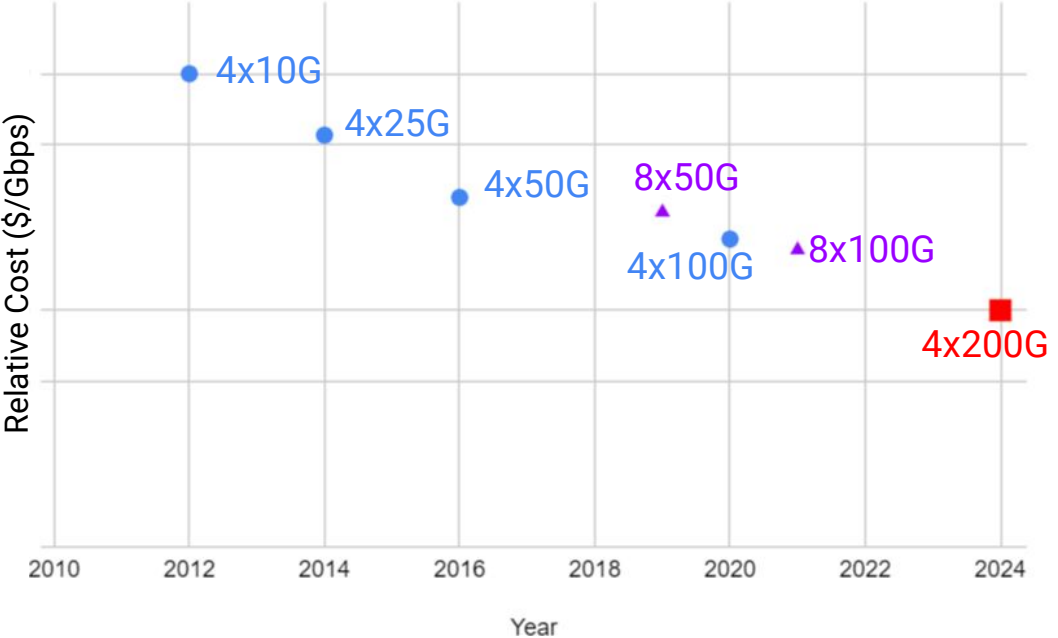


Backward compatibility between generations of interconnects enables smooth upgrade of datacenter networks.

# Why 200G per Lane?

- Cost efficiency for 800G
  - 4x200G
- Path to 1.6Tb & 3.2Tb per port
  - OSFP
  - OSFP-DD
  - CPO

# Cost/Gbps vs. Speed per Optical Lane



- **Faster optical lane speed is key to lower costs, but needs to align with electrical I/O speed for best cost & power efficiency**

# Implementation Comparison of 800G

	IM-DD PAM (8 lanes )	IM-DD PAM (4 lanes)
<b>Baud Rate (Gbaud)</b>	56G	~112G
<b>Number of Lasers</b>	8	4
<b>MZMs and Drivers</b>	8	4
<b>PD/TIAs</b>	8	4
<b>Relative DSP power</b>	1	~1.1 (stronger FEC and DSP )
<b>Link distance</b>	Limited by dispersion (2km, CWDM8)	Limited by dispersion (< 1km*, CWDM4)
<b>Fan out granularity</b>	100Gb/s	200Gb/s
<b>Scale to 1.6Tb/s and beyond</b>	No	Yes

\* Reach may be extended by more powerful DSP such as MLSE (Ilya Lyubomirsky, IEEE 2020 summer topical talk)

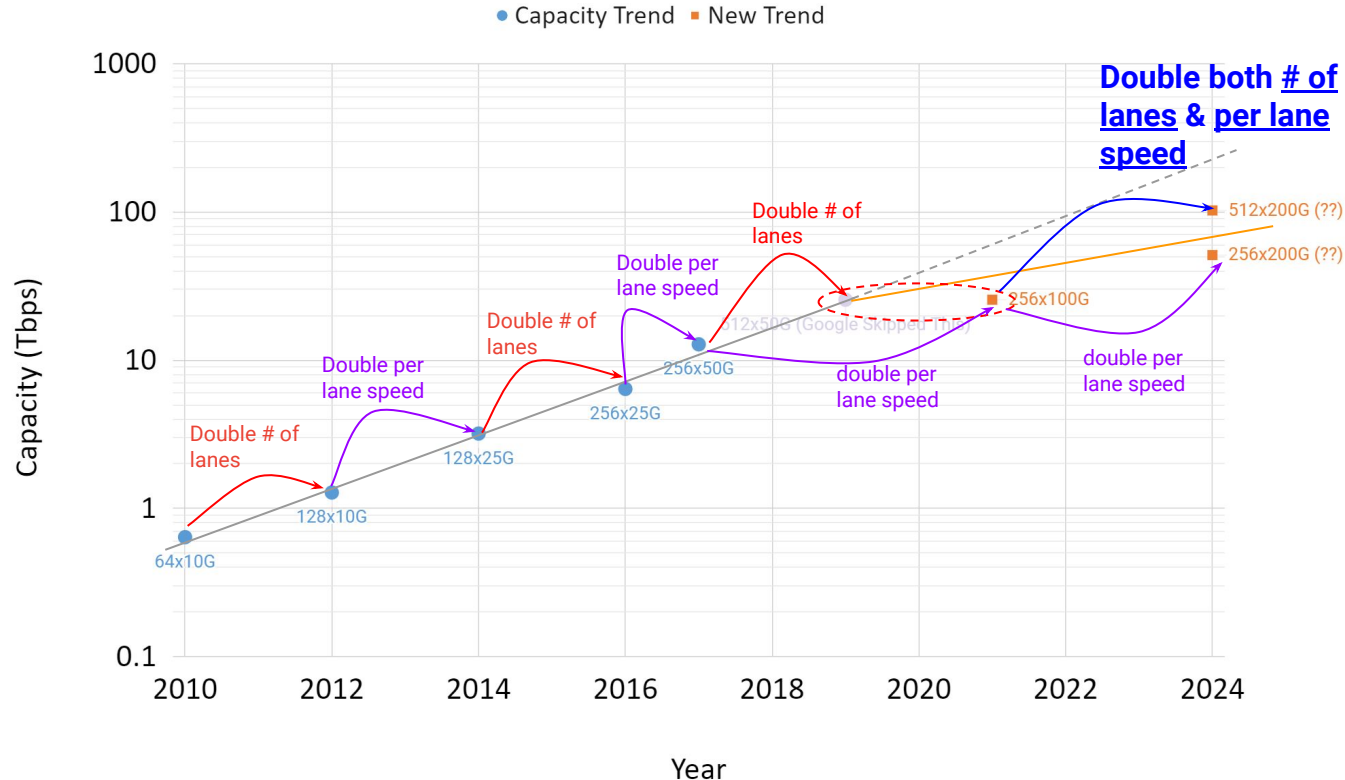
# Necessity of 200Gbps Electrical Lanes

- Scalability and visibility into 1.6T Ethernet
  - OSFP defined 8 electrical lanes
  - 8x 200G gives us 1.6Tb capacity
- Enable 100Tbps Switch ASIC
- Matching the electrical lane speed w/ optical lane speed
  - Simplifies module architectures
  - Reduces overall power consumption
  - Keeps the cost down in the long run
- Support for C2M, C2C and CR
  - Flexible, heterogeneous interconnects @lower cost
  - Better flexibility, serviceability and manufacturability in deployment





# 100Tbps Switch ASIC in 3 to 4 Years?



- Switch ASIC capacity growth slowed down but the demand is not.
  - New applications are emerging.
- It is harder to increase the number of lanes due to SI and # of packaging pins.
- Power consumption of switch ASIC is another concern



# 200G Optical Lane Technical Feasibilities

# System Model

## Focus on the following Functions/Blocks

- Two candidate modulation formats: PAM4 and PAM6
- 2 types of transmitters
  - InP EML
  - SiP MZM
- PD + TIA:  $R=0.8A/W$ ,  $IRN=16pA/\sqrt{Hz}$ , THD=3%
- Digital Electronics
  - 6-tap Tx FFE, 17-tap Rx-FFE, T-spaced
  - **FEC threshold  $4e-3$  assumed for 200Gb/s per lane\***

\* Ilya Lyubomirsky, "Coherent vs. Direct Detection for Next Generation Intra-Datacenter Optical Interconnects," IEEE 2020 summer topical

# Overall comparison: PAM4 vs PAM6

	PAM4	PAM6
Baud rate	~113Gbaud	~90Gbaud
Rx sensitivity penalty <sup>A</sup> @45GHz BW	~4.9dB	~3.3dB
Rx sensitivity penalty <sup>A</sup> @50GHz BW	~2.3dB	~2.4dB
Rx sensitivity penalty <sup>A</sup> @55GHz BW	~1.6dB	~2.2dB
Support 1km O-CWDM4 CD with EML	Yes CD penalty<1.5dB@55GHz	Yes CD penalty<1dB@55GHz
DAC/ADC ENOB requirement	~5.5 (stronger EQ)	~5.5 (higher-order mod.)
Relative DSP power	1	<1 ?

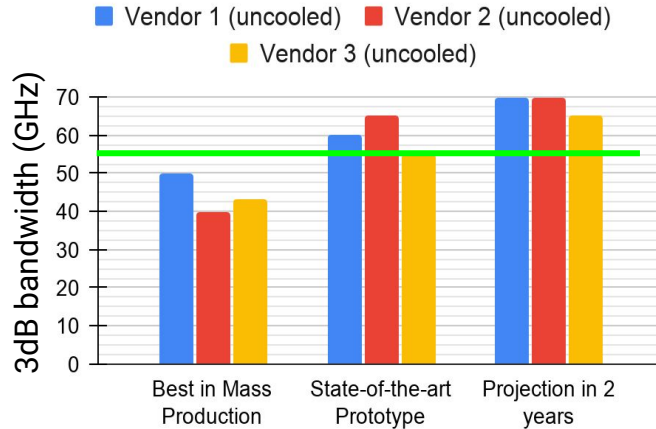
<sup>A</sup>: Compared to 106Gb/s per lane PAM4 with KP4 FEC

- **If PAM6 can achieve lower power, a dual-mode PAM4/PAM6 may be considered**
  - **PAM4 only for difficult links (higher link loss and/or MPI)**
  - **PAM6 for majority of the normal links to save overall network power**

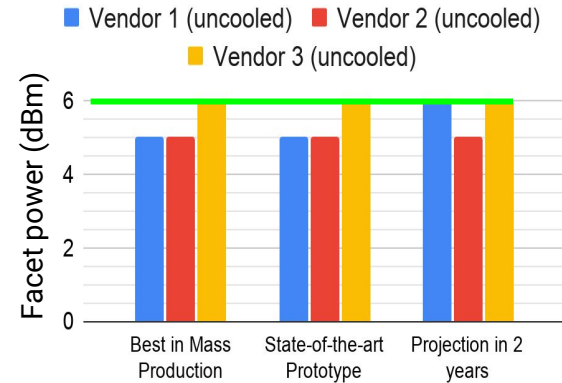
# 200Gb/s per optical lane components survey

## Transmitter 1: InP EML

### 3-dB Bandwidth



### Facet power (modulated)



— Preliminary requirements guideline to support 1km 800G CWDM4 reach

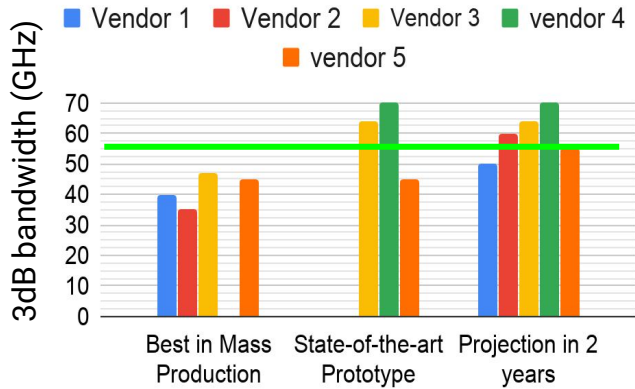
- Assume support both PAM4 and PAM6

- **Prototype: 1 (new) vendor** meets the preliminary guideline requirements for uncooled EML
  - July 2020, only 2 cooled prototypes met the preliminary requirements.
- **2-year projected: 4-2 vendors** meet the preliminary guideline requirements for uncooled EML

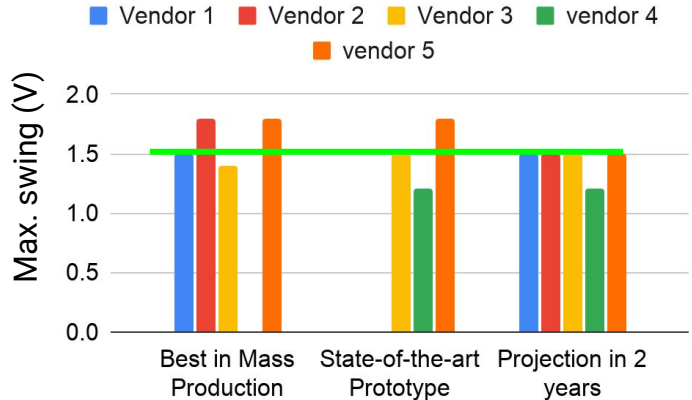
# 200Gb/s per optical lane components survey

## Transmitter 1 : EML Driver

### 3-dB Bandwidth



### Drive swing

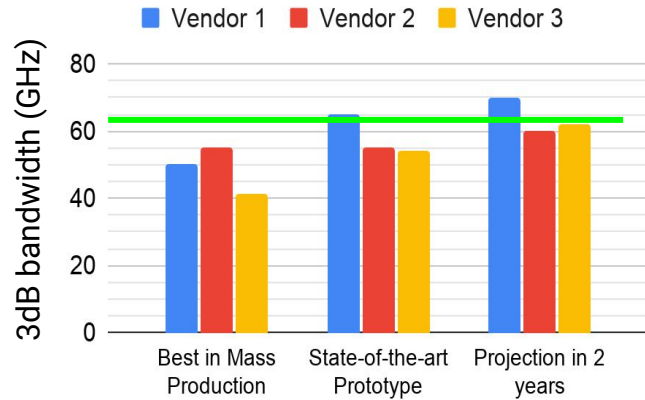


- **Prototype:** 1 vendor meets the preliminary guideline requirements
- **2-year projected:** 3 vendors meet the preliminary guideline requirements

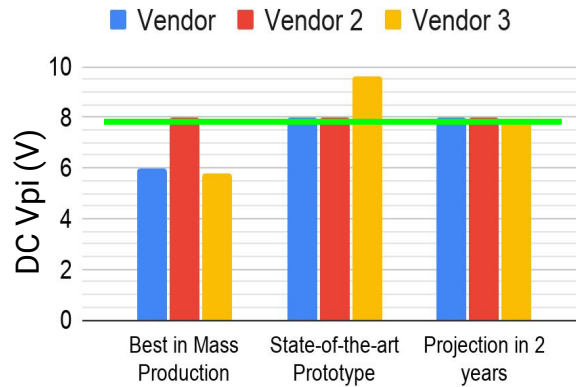
# 200Gb/s per optical lane components survey

## Transmitter 2: SiP-MZM

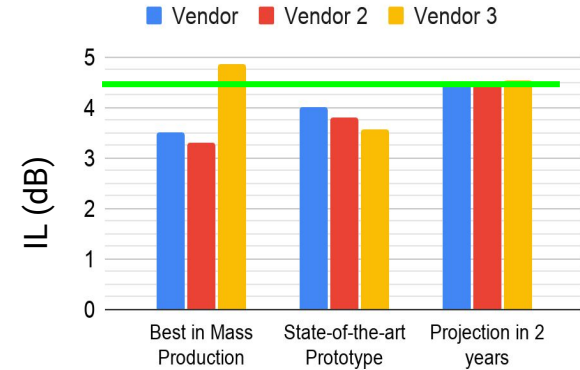
### 6-dB Bandwidth



### DC Vpi



### Insertion loss (dB)

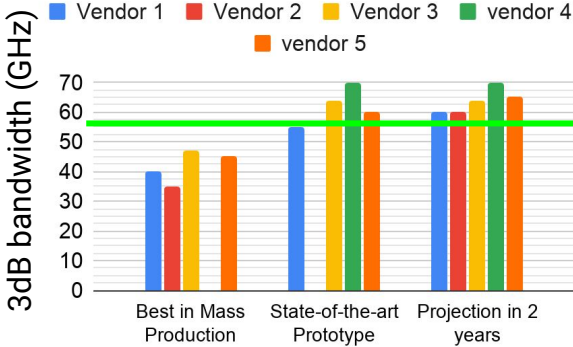


- **Prototype:** 1 (new) vendor meets the preliminary guideline requirements for DR reach
- **2-year projected:** + 2 vendor meets the preliminary guideline requirements for DR reach

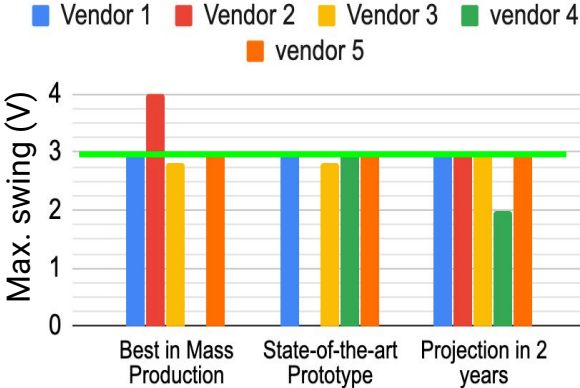
# 200Gb/s per lane components survey

## Transmitter 2: SiP-MZM driver

### 3-dB Bandwidth



### Drive output swing

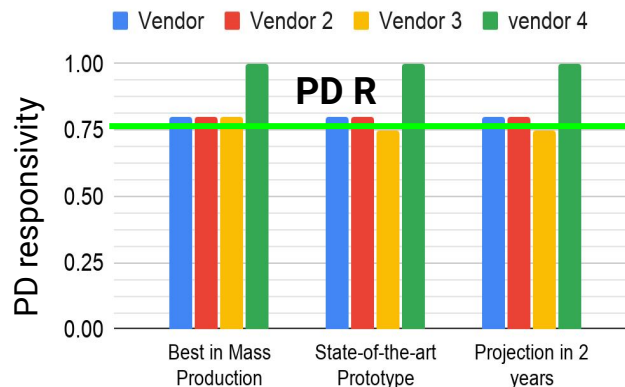
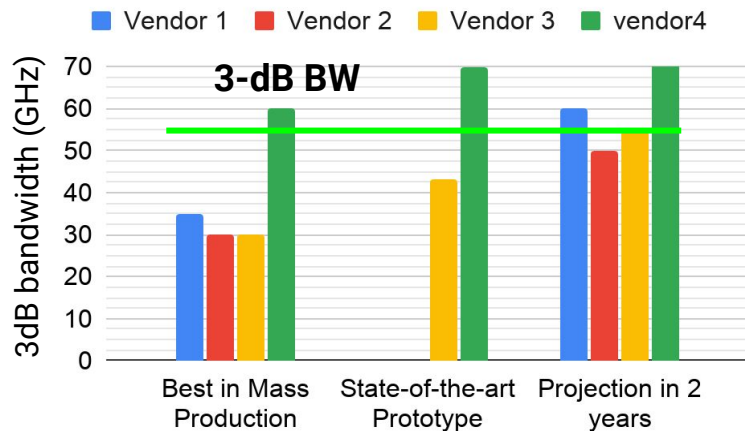


- **Prototype:** 3 vendor meets the preliminary guideline requirements
- **2-year projected:** 4 vendors meet the preliminary guideline requirements



# 200Gb/s per optical lane components survey

## Receiver: PD+TIA

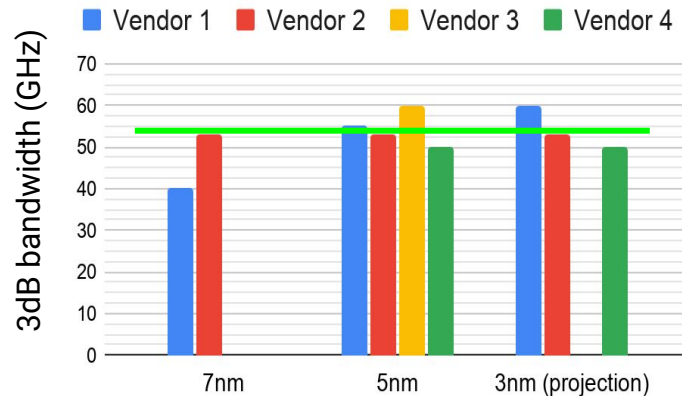


- **Prototype:** 1 (new) vendor meets the preliminary guideline requirements
- **2-year projected:** 3 vendors meet the preliminary guideline requirements

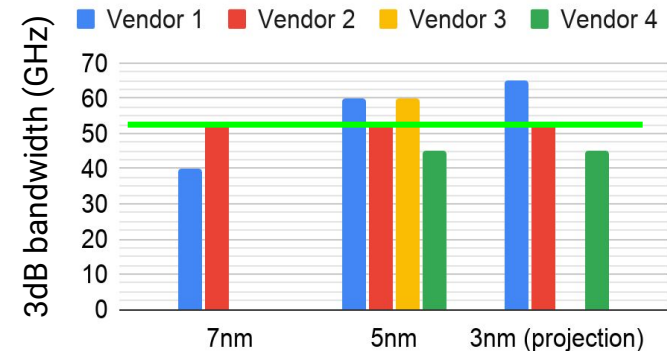
# 200Gb/s per optical lane components survey

## Digital Electronics: CMOS DAC and ADC

### DAC



### ADC



- **5nm CMOS:** 2-3 vendors meet the preliminary BW guideline requirements
- **3nm CMOS:** main purpose to reduce power consumption

# 200G/s per Lane Technology Improvements

	Vendor	Parameter	July 2020 Survey		March 2021 Survey	
			Best Prototype	2-year Projection	Best Prototype	2-year Projection
Tx 1 (InP EML)	2	EML 3dB BW(GHz), uncooled	60	70	65	70
	3	EML 3dB BW (GHz)	43	47	55	65
		Cooled or uncooled EML	Cooled	Cooled	Uncooled	Uncooled
Tx 2 (SiPh- MZM)	New Vendor	6dB-BW (GHz)			54.1	62
		DC Vpi (V)			9.6	7.9
		Intrinsic Insertion loss (dB)			3.6	4.5
Tx 2 MZM Driver	5	3dB BW (GHz)	45	55	60	65
Rx (PD+TIA)	3	3dB BW (GHz)	43	50	43	55
	4	3dB BW (GHz)	N.A	70	70	80
Digital	3	5nm DAC BW (GHz)	~47.5	N.A	~60	N.A

# 200Gb/s per Optical Lane Components Readiness

For 500m DR4 (3dB) and 1km CWDM4 (4dB)

		Mass Production	Prototype	2-year Projected
Transmitter 1 InP EML	InP EML	✗	✓ (uncooled) July 2020: only cooled March 2021: uncooled	✓ (uncooled)
	EML Driver	✗	✓	✓
Transmitter 2 SiP MZM	MZM (SiPh)	✗	✗ Ready for DR-reach	Ready for DR-reach
	MZM Driver	✗	✓	✓
Receiver	PD / TIA	✗	✗ ✓	✓
Electronics	CMOS DSP	✗ (7nm)	✓ (5nm)	✓ (5nm/3nm)

# Conclusions

- Demands for datacenter bandwidths keep growing quickly.
- It is right time to develop the next higher-speed Ethernet beyond 400GbE
- For intra-datacenter applications, 200Gbps per lane IM-DD implementation provides:
  - Lower TCO
  - Pathway to 1.6Tbps Ethernet
- Technical feasibility of 200Gbps per optical lane is within the reach in the next two years
  - Well within the time frame to complete the next higher-speed Ethernet standard